



Product Summary

The ZM8810T combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

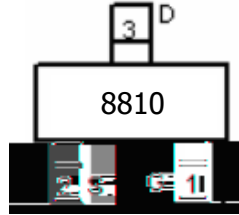
$$V_{DS} = 20V$$

$$R_{DS(ON)} = 16m\Omega$$

$$I_D = 7A$$



high cell density Trench technology
 $R_{DS(ON)}$ to minimize conductive loss



SOT23-3

Load Switch
 PWM Application

Part NO.	ZM8810T
Marking	ZM8810
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

$T_C = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 8	V
Continuous Drain Current	$I_{D@TC=25^\circ C}$	7	A
	$I_{D@TC=75^\circ C}$	5.3	A
	$I_{D@TC=100^\circ C}$	4.4	A
Pulsed Drain Current ①	I_{DM}	25	A
Total Power Dissipation	P_D	12	W
Total Power Dissipation($T_A=25^\circ C$)	$P_{D@TA=25^\circ C}$	0.75	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$

**Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	10	C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	170	C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	C

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	0.45	0.6	1	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=16V, V_{GS}=0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 8V, V_{DS}=0V$			± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=4.5V, I_D=6A$		16	20	m Ω
		$V_{GS}=2.5V, I_D=6A$		19	25	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=10V, I_D=1A$		50		s
Source-drain voltage	V_{SD}	$I_S=6A$			1.28	V



Fig.1 Power Dissipation Derating Curve

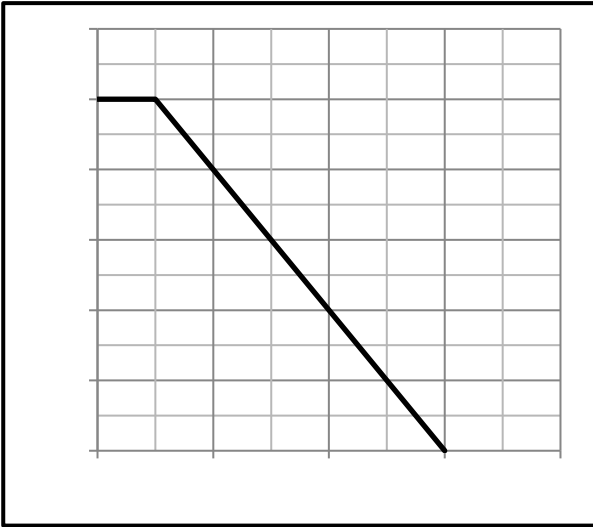


Fig.2 Typical output Characteristics

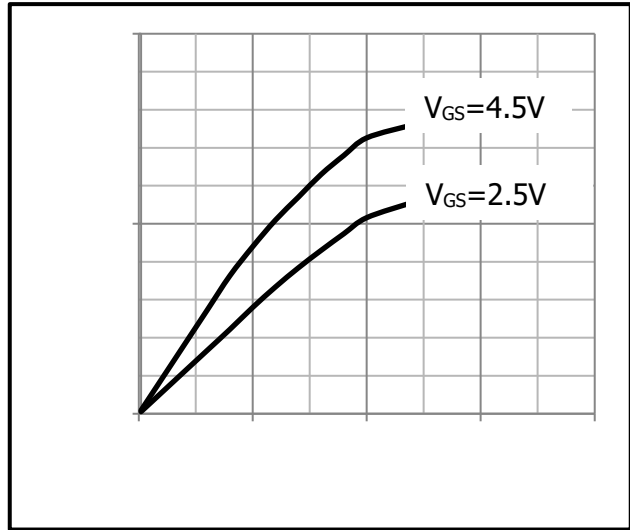


Fig.3 Threshold Voltage V.S Junction Temperature Fig.4 Resistance V.S Drain Current

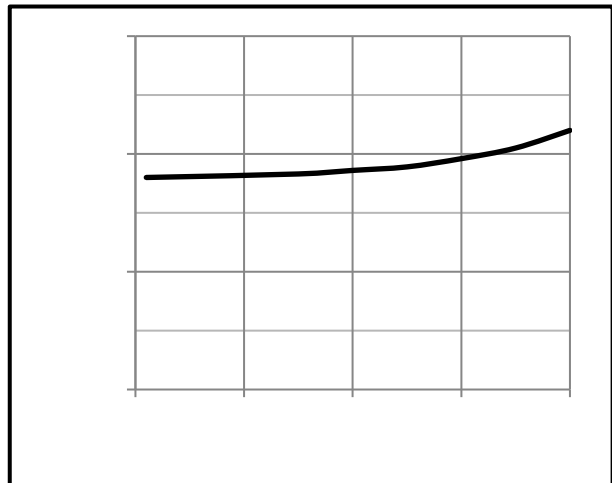
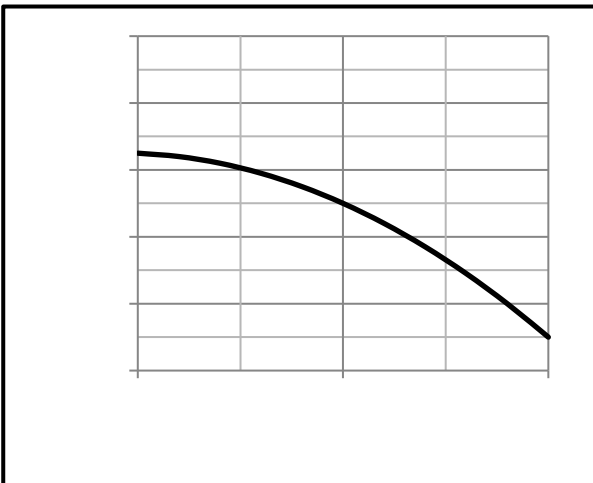


Fig.5 On-Resistance VS Gate Source Voltage

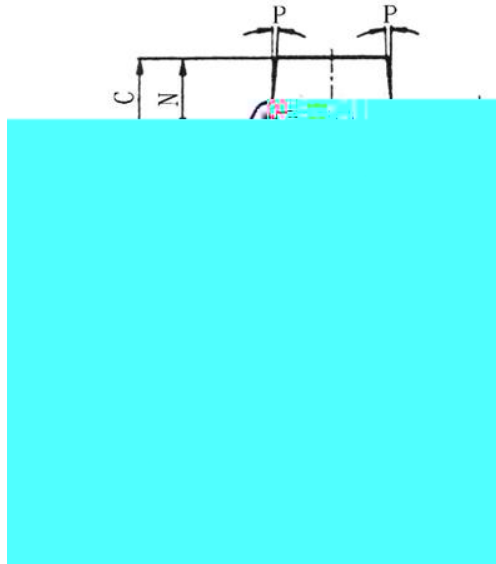
Fig.6 On-Resistance V.S Junction Temperature





(SOT23-3)

Unit mm



SYMBOL	min	nom	max
A	2.70	2.9	3.10
B	1.15	1.3	1.50
C			1.30
D	0.35	0.4	0.55
E	2.20	2.4	2.70
G	1.70	1.9	2.10
H	0.85	0.95	1.05
J	0.05	0.10	0.20



K	0.00		0.10
L	0.45	0.55	0.65
M	0.20		
N	0.90	1.00	1.20
P		7°	